

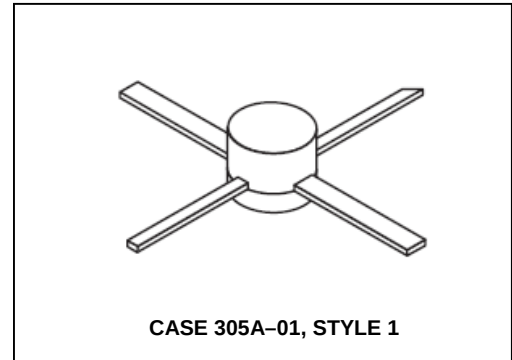
The RF Line NPN Silicon High-Frequency Transistor 1.0W, 400MHz, 28V

M/A-COM Products
Released - Rev. 07.07

Designed for wideband amplifier, driver or oscillator applications in military, mobile, and aircraft radio.

- Specified 28 V, 400 MHz characteristics —
Output power = 1.0 W
Power gain = 15 dB min.
Efficiency = 45% typ.
- Emitter ballast and low current density for improved MTBF
- Common emitter for improved stability

Product Image



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Collector Current — Continuous	I_C	150	mAdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	6.1 35	Watts mW/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	28.5	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	30	—	—	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 5.0$ mAdc, $V_{BE} = 0$)	$V_{(BR)CES}$	35	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 0.1$ mAdc, $I_E = 0$)	$V_{(BR)CBO}$	35	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 1.0$ mAdc, $I_C = 0$)	$V_{(BR)EBO}$	3.0	—	—	Vdc
Collector Cutoff Current ($V_{CE} = 20$ Vdc, $I_B = 0$)	I_{CEO}	—	—	1.0	mAdc

(continued)

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ELECTRICAL CHARACTERISTICS — continued ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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ON CHARACTERISTICS

DC Current Gain ($I_C = 100\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$)	h_{FE}	20	60	150	—
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DYNAMIC CHARACTERISTICS

Current-Gain — Bandwidth Product ($I_C = 100\text{ mAdc}$, $V_{CE} = 20\text{ Vdc}$, $f = 200\text{ MHz}$)	f_T	—	2.5	—	GHz
Output Capacitance ($V_{CB} = 28\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{ob}	—	3.5	5.0	pF

FUNCTIONAL TESTS

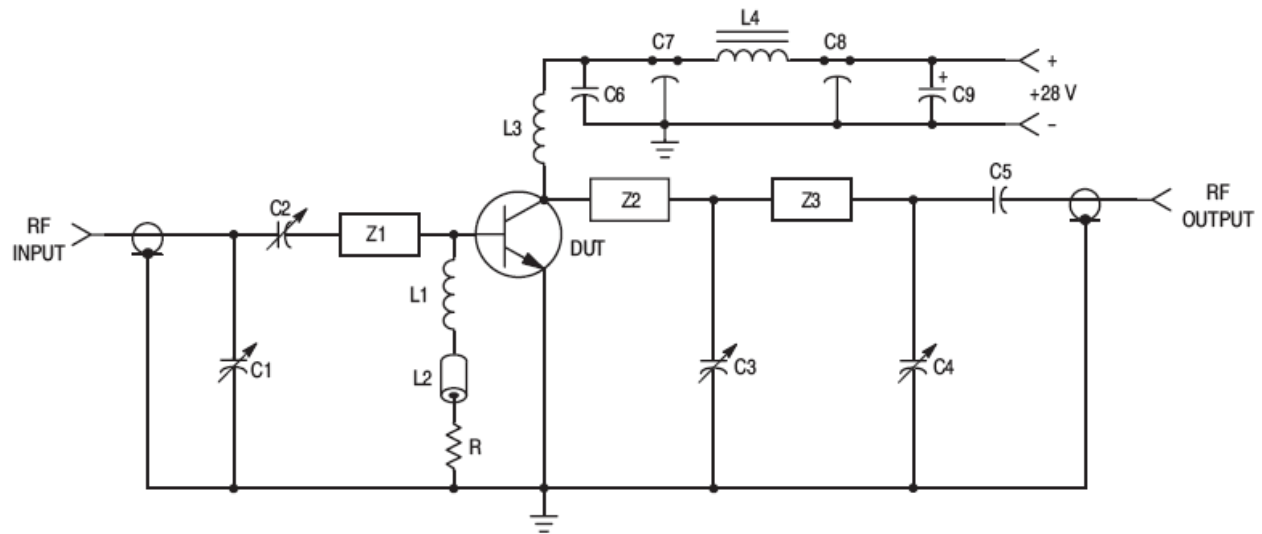
Common-Emitter Amplifier Power Gain (1) ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 1.0\text{ W}$, $f = 400\text{ MHz}$)	G_{pe}	15	16	—	dB
Collector Efficiency ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 1.0\text{ W}$, $f = 400\text{ MHz}$)	η	—	45	—	%
Series Equivalent Input Impedance ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 1.0\text{ W}$, $f = 400\text{ MHz}$)	Z_{in}	—	$6.4 - j4.8$	—	Ohms
Series Equivalent Output Impedance ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 1.0\text{ W}$, $f = 400\text{ MHz}$)	Z_{out}	—	$75 - j45$	—	Ohms

NOTE:

1. Class C

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C1, C2, C4 — 1.0–20 pF JOHANSON 9063
C3 — 1.0–10 pF JOHANSON
C5 — 150 pF Chip
C6 — 0.1 μ F
C7, C8 — 680 pF Feedthru
C9 — 1.0 μ F TANTALUM

L1, L3 — 5 Turns, AWG #20, 1/4" I.D.
L2 — Ferrite Bead, FERROXCUBE
No. 56–590–65/4B
L4 — FERROXCUBE VK200–20/4B
Input/Output Connectors — Type N
Board — Glass Teflon, $\epsilon = 2.56$, $t = 0.062$ "

R — 4.7 Ohms, 1/4 W
Z1 — 2.0" x 0.1" MICROSTRIP LINE
Z2, Z3 — 2.6" x 0.1" MICROSTRIP LINE

Figure 1. 400 MHz Power Gain Test Circuit

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PACKAGE DIMENSIONS

